

PROGRAM

2005 IEEE Workshop on Charge-Coupled Devices and Advanced Image Sensors

Thursday, June 9

- 8:30–8:45 **Opening Remarks** N. Teranishi
- Session 1. Small Pixel Sensors(1)**
Chairman S.G. Wu (TSMC)
- 8:45
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J. Adkisson, J. Gambino, T. Hoague, M. Jaffe, J. Kyan*, R. Leidy*,
D. McGrath*, R. Rassel, D. Sackett* and C. V. Stancampiano*
IBM Corporation, USA
*Eastman Kodak Company, USA
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J.S. Lin*, L.L. Yao*, W.D. Wang*, C.Y. Yu*, C.H. Lo* and C.S. Wang*
National Cheng Kung University, Taiwan, R.O.C.
*Taiwan Semiconductor Manufacturing Company, Taiwan, R.O.C.
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R.D. McGrath, H. Fujita, R.M. Guidash, T.J. Kenney and W. Xu
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M. Kojima, Y. Matsunaga and S. Mayumi
Matsushita Electric Industrial Co., Ltd., Japan
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T. Lulé, R. Henderson*, L. Simony, F. Mütze, S. Benthien and M. Sommer
ST Microelectronics, France
*University of Edinburgh, UK

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Texas Instruments Japan, Japan
*Graduate School of Engineering, Tohoku University, Japan
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Micron Technology, Inc., USA

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R32 **N. Karasawa, D. Sugimoto, H. Ohki, K. Hatano* and H. Yoshida****
Sony Corporation, Japan
*Sony Semiconductor Kyusyu Corporation, Japan
**Sony LSI Design Inc., Japan

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E.R. Fossum
Siimpel Corporation, USA
University of Southern California, USA
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19:00–21:00

Session 11. Walter Kosonocky Award Presentation, Dinner
Chairman N. Teranishi (Matsushita)

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M. Sasaki, M. Mase*, S. Kawahito* and Y. Wakamori**
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